



# SC0565 SC0565F SC0565D2

SILICON CARBIDE SCHOTTKY DIODE  
Reverse Voltage - 650 Volts  
Forward Current - 5.0Amperes

## DESCRIPTION

SiC Schottky Diode has no switching loss, provides improved system efficiency against Si diodes by utilizing new semiconductor material-Silicon Carbide, enables higher operating frequency, and helps increasing power density and reduction of system size /cost. Its high reliability ensures robust operation during surge or over-voltage conditions.

## FEATURES

- Max Junction Temperature 175°C
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery

## MECHANICAL DATA

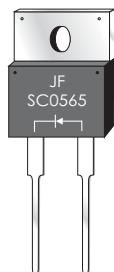
- Case: JEDEC TO-220AC/ITO-220AC/TO-263AC
- Molding compound meets UL94V-0 flammability rating
- Terminals: Lead solderable per J-STD-002 and JESD22-B102
- Polarity: As marked
- Mounting Torque: 10 in-lbs maximum

## TYPICAL APPLICATIONS

- General Purpose
- SMPS, Solar inverter, UPS
- Power Switching Circuits

### TO-220AC

**SC0565**



### ITO-220AC

**SC0565F**



### TO-263AC

**SC0565D2**



## MAXIMUM RATINGS

(Ratings at 25°C ambient temperature unless otherwise specified )

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	$V_{RRM}$	650	V
Continuous Rectified Forward Current	$I_F$	5	A
Repetitive Forward Surge Current(NOTE 1)	$I_{F,RM}$	30	A
Operating junction temperature range	$T_J$	-55 to +175	°C
Storage temperature range	$T_{stg}$	-55 to +175	°C

Notes: 1.Half-Sine Pulse,  $t_p=8.3\text{ms}$

## RATINGS AND CHARACTERISTIC

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### ELECTRICAL CHARACTERISTICS ( $T_A=2^\circ\text{C}$ Unless otherwise noted)

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Parameter	Test Conditions		Symbol	TYP.	MAX.	Unit
Instantaneous forward voltage	$I_F=5\text{A}$	$T_A=25^\circ\text{C}$	$V_F$	1. 6	1. 8	V
		$T_A=175^\circ\text{C}$		1. 8	2. 0	
Reverse current	$V_R=650\text{V}$	$T_A=25^\circ\text{C}$	$I_R$	–	10	$\mu\text{A}$
		$T_A=125^\circ\text{C}$		–	40	
		$T_A=175^\circ\text{C}$		–	100	
Typical junction capacitance	$V_R=1\text{V}, f=100\text{kHz}$		$C_j$	208	–	$\text{pF}$
	$V_R=10\text{V}, f=100\text{kHz}$			90	–	
	$V_R=40\text{V}, f=100\text{kHz}$			45	–	

### THERMAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ Unless otherwise noted)

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Parameter	Symbol	Value	Unit
Typical thermal resistance <sup>2)</sup>	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$

2.Thermal resistance from junction to case

## RATINGS AND CHARACTERISTIC

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FIG.1-FORWARD CURRENT DERATING CURVE

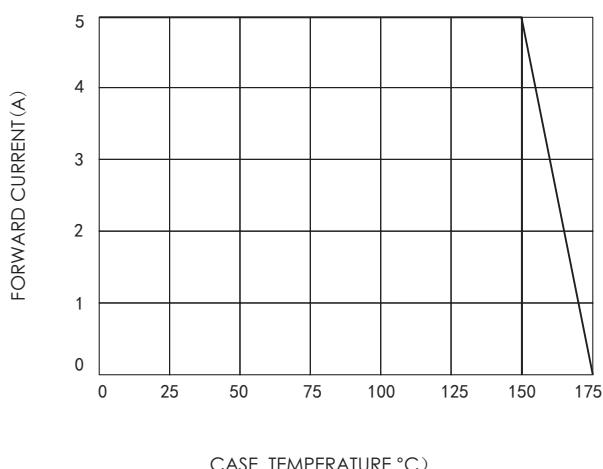


FIG.2-TYPICAL JUNCTION CAPACITANCE

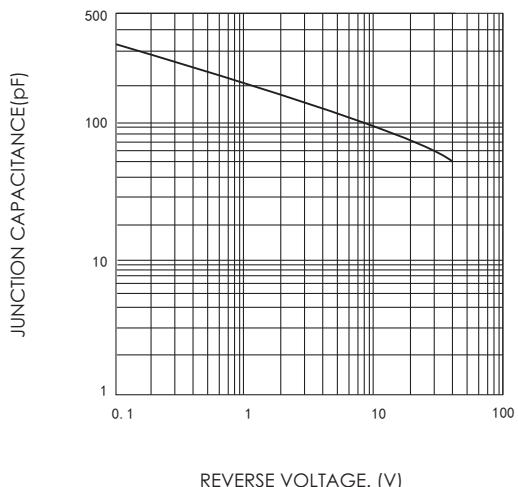


FIG.2-FORWARD CHARACTERISTICS

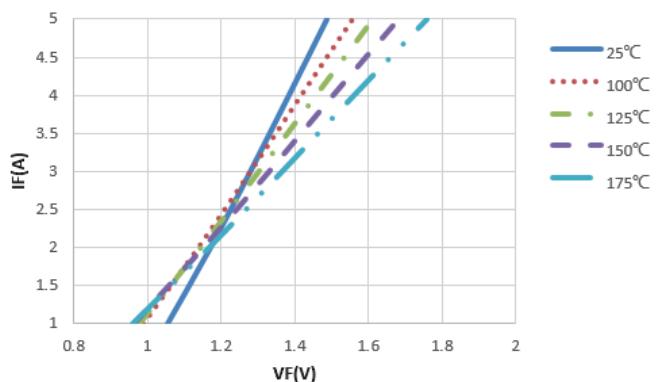
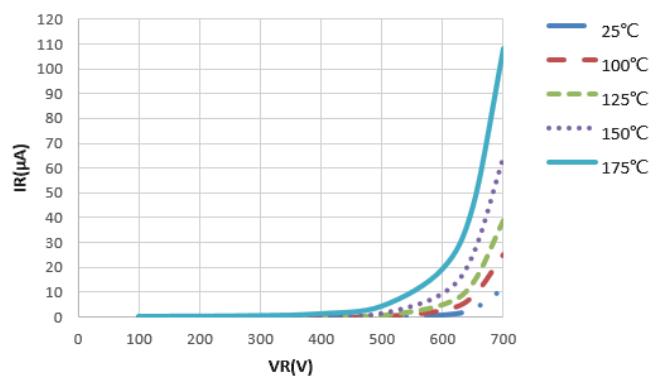


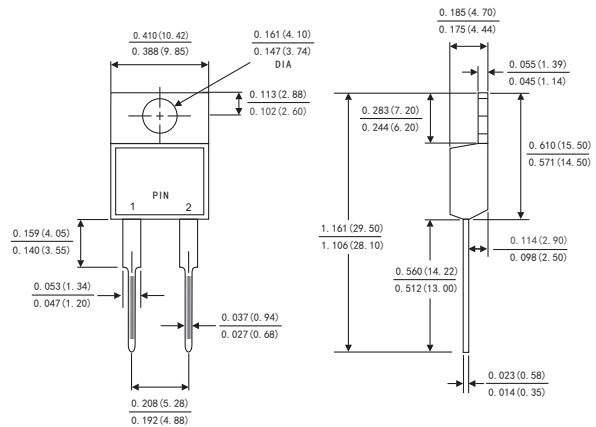
FIG.4-REVERSE CHARACTERISTICS



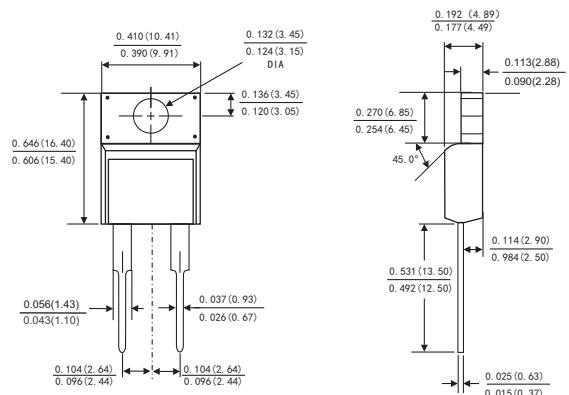
## PACKAGE OUTLINE DIMENSIONS

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**TO-220AC**



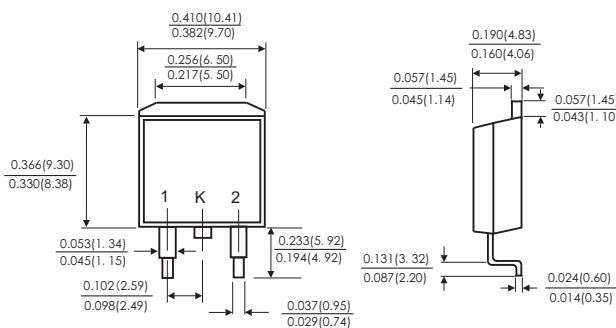
**ITO-220AC**



Dimensions in inches and (millimeters)

Dimensions in inches and (millimeters)

**TO-263AC  
D2PAK**



Dimensions in inches and (millimeters)